CBSL1SL

NPN SILICON RF POWER TRANSISTOR

DESCRIPTION:

The **ASI CBSL1SL** is Designed for Class A, Cellular Base Staion Applications up to 960 MHz.

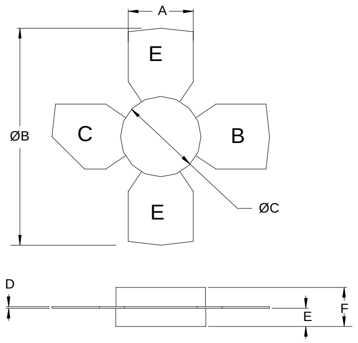
FEATURES:

- Class A Operation
- **P_G** = 10 dB at 1.0 W/960 MHz
- ***Omnigold***™ Metalization System

MAXIMUM RATINGS

I_C	0.250 A
V_{CBO}	40 V
V_{CEO}	28 V
V_{EBO}	3.5 V
P_{DISS}	7.0 W @ T_C = 25 °C
T_J	-65 °C to +200 °C
T_{STG}	-65 °C to +150 °C
θ_{JC}	25 °C/W

PACKAGE STYLE .280 4L PILL



DIM	MINIMUM inches / mm	MAXIMUM inches / mm
A	.220 / 5.59	.230 / 5.84
B		1.055 / 26.80
C	.275 / 6.99	.285 / 7.24
D	.004 / 0.10	.006 / 0.15
E	.050 / 1.27	.060 . 1.52
F	.118 / 3.00	.130 / 3.30

ORDER CODE: ASI10578

CHARACTERISTICS T_C = 25 °C

SYMBOL	TEST CONDITIONS	MINIMUM	TYPICAL	MAXIMUM	UNITS
BV_{CBO}	I_C = 1.0 mA	40			**V**
BV_{CEO}	I_C = 1.0 mA	28			**V**
BV_{EBO}	I_E = 1.0 mA	3.5			**V**
I_{CBO}	V_{CB} = 24 V			0.5	**mA**
h_{FE}	V_{CE} = 5.0 V I_C = 100 mA	20		120	**---**
C_{OB}	V_{CB} = 24 V f = 1.0 MHz			5.0	**pF**
P_G	V_{CC} = 24 V I_{CQ} = 125 mA f = 960 MHz P_{OUT} = 1.0 W	10			**dB**